

IN THE CLAIMS:

Amend claims 1 and 5 as follows:

Sub 1
1. (Amended) A fabrication method of a semiconductor device comprising the steps of:

(a) forming a [given number] plurality of projection electrodes on each of a [given number] plurality of semiconductor chips, and applying a thermosetting insulating adhesive to areas of mounting parts where the semiconductor chips are to be mounted on a substrate;

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(b) heating said thermosetting insulating adhesive on said substrate with a half-thermosetting temperature so as to retain a degree of viscosity of said thermosetting insulating adhesive, and, concurrently,; (c) aligning said semiconductor chips to said mounting parts of the substrate, and performing a first fixing of the semiconductor chips with a first pressure; and

[(d)] (c) thereafter heating said substrate, on which said semiconductor chips are fixed, with a thermosetting temperature of said thermosetting insulating adhesive, and performing a second fixing of the semiconductor chips with a second pressure.

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5. (Amended) The fabrication method of the semiconductor device as claimed in claim ~~1~~ ¹⁵, wherein said [given

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number] plurality of the projection electrodes are formed as studs by wire-bonding, the studs being leveled.

REMARKS

The specification, and claims 1 and 5 have been amended in order to more particularly point out, and distinctly claim the subject matter to which the applicants regard as their invention. It is believed that this Amendment is fully responsive to the Office Action dated February 16, 1996.

The specification has been objected to under 35 USC 112, first paragraph, for the reasons specifically set forth starting from line 14, page 2 through line 21, page 3 of the outstanding Action. The applicants respectfully request reconsideration of these objections.

As indicated above, the specification has been amended in order to address the Examiner's objections thereto. More particularly, pages 5 and 11 of the applicants' specification have been amended in order to clarify that in the first fixing, the semiconductor is not pressed to the substrate with a strong pressure, but at the second fixing, the semiconductor chip is pressed to the substrate with a strong second pressure larger than the first pressure. Therefore, by the second pressure, the